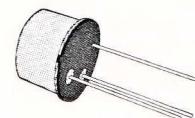


## HIGH VOLTAGE AMPLIFIER

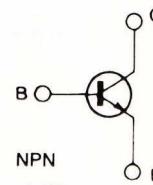
### DESCRIPTION

The 2N3114 is a silicon planar epitaxial NPN transistor in Jedec TO-39 metal case. It is primarily intended for high voltage, medium power applications.



TO-39

### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-base Voltage ( $I_E = 0$ )	150	V
$V_{CEO}$	Collector-emitter Voltage ( $I_B = 0$ )	150	V
$V_{EBO}$	Emitter-base Voltage ( $I_C = 0$ )	5	V
$I_C$	Collector Current	150	mA
$P_{tot}$	Total Power Dissipation at $T_{amb} \leq 25^\circ C$	0.8	W
	at $T_{case} \leq 25^\circ C$	5	W
$T_{stg}, T_j$	Storage and Junction Temperature	65 to 200	°C

## THERMAL DATA

$R_{th\ j\text{-case}}$	Thermal Resistance Junction-case	Max	35	$^{\circ}\text{C/W}$
$R_{th\ j\text{-amb}}$	Thermal Resistance Junction-ambient	Max	219	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ( $T_{amb} = 25^{\circ}\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CBO}$	Collector Cutoff Current ( $I_E = 0$ )	$V_{CB} = 100\text{ V}$ $V_{CB} = 100\text{ V}$ $T_{amb} = 150^{\circ}\text{C}$			10 10	nA $\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current ( $I_C = 0$ )	$V_{EB} = 4\text{ V}$			100	nA
$V_{(BR)CBO}$	Collector-base Breakdown Voltage ( $I_E = 0$ )	$I_C = 100\text{ }\mu\text{A}$	150			V
$V_{(BR)CEO}^*$	Collector-emitter Breakdown Voltage ( $I_B = 0$ )	$I_C = 10\text{ mA}$	150			V
$V_{(BR)EBO}$	Emitter-base Breakdown Voltage ( $I_C = 0$ )	$I_E = 100\text{ }\mu\text{A}$	5			V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 50\text{ mA}$ $I_B = 5\text{ mA}$			1	V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = 50\text{ mA}$ $I_B = 5\text{ mA}$			0.9	V
$h_{FE}^*$	DC Current Gain	$I_C = 100\text{ }\mu\text{A}$ $V_{CE} = 10\text{ V}$ $I_C = 30\text{ mA}$ $V_{CE} = 10\text{ V}$ $T_{amb} = -55^{\circ}\text{C}$ $I_C = 30\text{ mA}$ $V_{CE} = 10\text{ V}$	15 30 12	35 60 24	120	
$h_{fe}$	High Frequency Current Gain	$I_C = 30\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 20\text{ MHz}$	2			
$C_{EBO}$	Emitter-base Capacitance	$V_{EB} = 0.5\text{ V}$ $f = 1\text{ MHz}$			80	pF
$C_{CBO}$	Collector-base Capacitance	$V_{CB} = 20\text{ V}$ $f = 1\text{ MHz}$			9	pF

\* Pulsed : pulse duration = 300  $\mu\text{s}$ , duty cycle = 1 %.